

AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph beginning at page 15, line 4, with the following rewritten paragraph:

B¹
--Thereafter, a lower dielectric layer ~~131~~ 13 containing a low melting point glass as a main constituent is formed to cover the lower electrodes 121 and, further, upper electrodes 122 of a transparent, electrically conductive material such as the above mentioned ITO are formed on the lower dielectric layer 13 correspondingly in position to the lower electrodes 121.--

Please replace the paragraph beginning at page 17, line 3, with the following rewritten paragraph:

B²
--Each of embodiments shown in FIGS. 3A and 3B and FIGS. 4A, 4B and 4C differs from the embodiments shown in FIGS. 1A and 1B and FIGS. 2A and 2B in that the lower dielectric layer ~~13~~ 23 is partially formed on the first glass substrate 11 such that it covers at least the sustain gap between the lower electrodes 121. The upper electrodes 122 on a lower dielectric layer 23 such that it is separated from the lower electrodes 121 by the dielectric layer 23.--

Please replace the paragraph beginning at page 20, line 10, with the following rewritten paragraph:

B³
--First, the first embodiment of the present invention will be described with reference to FIGS. 6A and 7B ~~6B~~ and FIGS.

B3
Circled


7A and 7B. It should be noted that, in FIGS. 6A and 6B to FIGS. 17A and 17B, an even numbered figure and a subsequent odd numbered figure are paired to show the features of one embodiment of the present invention. In each embodiment, the figure having affix A is a plan view and the figure having affix B is a cross section taken along a line A-A' or B-B' in the figure having affix A to clarify a difference thereof from the other embodiments.--

Please replace the paragraph beginning at page 23, line 11, with the following rewritten paragraph:

B4

--In the second embodiment, a lower dielectric layer 23 is formed partially on the first glass substrate 11 such that the lower dielectric layer 23 covers at least a sustain gap between the inner ends of the opposing lower ~~electrodes 121~~ and electrodes 121 and the upper ~~electrodes 122~~ electrodes 122 are formed on the lower dielectric layer 23 such that the upper electrodes 122 correspond to the lower electrodes 121, respectively, as shown in FIG. 8B and 9B. In order to connect the upper electrodes 122 to the respective lower electrodes 121 and to reduce a resistance of a connecting wiring from the electrodes 121 and 122, a low resistance wiring 220 is formed of a low resistance material as shown in FIG. 9B.--

Please replace the paragraph beginning at page 25, line 7, with the following rewritten paragraph:

 --In the fourth embodiment, the lower electrodes ~~121~~
221 are formed separately from low resistance wiring 420 and
connected to the upper electrodes 122 and the low resistance
wiring 420 through a connecting wiring 423 in regions
corresponding to the partition wall regions 31 of the second
glass substrate as shown in FIG. 13B. In this embodiment, the
connecting wiring 423 and the low resistance wiring 420 are
formed simultaneously. However, the connecting wiring 423 may be
formed in other step than that of forming the low resistance
wiring 420. Furthermore, in this embodiment, the same material
may be used to form both the connecting wiring ~~223~~ 423 and the
upper electrodes 122. Alternatively, it is possible to unite the
upper electrodes 122, the connecting wiring 423 and the low
resistance wiring 420.--
